1.4c SiO₂, SiNx and Amorphous-Si Chamber Clean (NF₃)

Mode: PE
Pumps: Mechanical
Susceptor Material: Aluminum
Temperature (°C): Same as Deposition Process

Electrode Size: 6" 8" 11"

Gases (sccm):

NF₃  75  115  150
N₂   25  35   50

Pressure (mTorr): 150 150 150
Power (Watts): 300 350 400
DC-bias (Volts):

Typical Etch Rate (Å/min.) up to 2000

Notes:
Before continuing deposition work, a pre-deposition run of 500-1000Å should be performed to condition the chamber.

NF₃ is frequently difficult to tune so N₂ has been added to this process to give it stability. If tuning is difficult, the amount of N₂ can be increased.